

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	893	(WATANABE near2 MASANORI).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:20
S5	0	laser and (clad near3 (Al near5 Ga near5 In near5 P)) and (active near3 (Al near5 Ga near5 In near5 P)) and (((band near2 gap) or bandgap) near3 (Al near5 Ga near5 In near5 P)) and oxide and (cap near3 (Al near5 Ga near5 As)) and (contact near3 (Al near5 Ga near5 As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:36
S8	4	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and (Al near5 Ga near5 In near5 P) and (Al near5 Ga near5 As)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:38
S7	0	laser and (clad\$4 near3 (Al near5 Ga near5 In near5 P)) and (active near3 (Al near5 Ga near5 In near5 P)) and (((band near2 gap) or bandgap) near3 (Al near5 Ga near5 In near5 P)) and oxide and (cap near3 (Al near5 Ga near5 As)) and (contact near3 (Al near5 Ga near5 As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:38
S14	0	(semiconductor near3 laser) and (clad\$4 near5 (Al with Ga with In with P)) and (active near5 (Al with Ga with In with P)) and (((band near2 gap) or bandgap) near5 (Al with Ga with In with P)) and oxide and (cap near5 (Al with Ga with As)) and (contact near5 (Al with Ga with As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:39
S13	0	(semiconductor near3 laser) and (clad\$4 near3 (Al with Ga with In with P)) and (active near3 (Al with Ga with In with P)) and (((band near2 gap) or bandgap) near3 (Al with Ga with In with P)) and oxide and (cap near3 (Al with Ga with As)) and (contact near3 (Al with Ga with As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:39
S12	0	laser and (clad\$4 near3 (Al with Ga with In with P)) and (active near3 (Al with Ga with In with P)) and (((band near2 gap) or bandgap) near3 (Al with Ga with In with P)) and oxide and (cap near3 (Al with Ga with As)) and (contact near3 (Al with Ga with As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:39
S16	2	("6670202").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 11:42
S15	2	("20030042492").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 11:42
S17	188	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:46
S3	18	S1 and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 11:51

S18	10	((("6,356,572") or ("5,573,976") or ("6,670,202") or ("20040066822") or ("5,070,510")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 11:52
S19	893	(WATANABE near2 MASANORI).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:15
S10	36	(semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and (Al with Ga with In with P) and (Al with Ga with As)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:15
S2	399154	S1 and "372"/\$.ccls. or "257"/\$.ccls. or "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:15
S23	1	S19 and delma near2 flores.xa.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:16
S22	5	(semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and delma near2 flores.xa.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:16
S20	49	S19 and ("257"/\$.ccls. or "438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:17
S25	6	(semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:18
S24	0	(semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and (Al with Ga with In with P) and (Al with Ga with As) and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:18
S21	1	(semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and (Al with Ga with In with P) and (Al with Ga with As) and delma near2 flores.xa.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:18
S6	403	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:50

S9	37	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and (Al with Ga with In with P) and (Al with Ga with As)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 12:53
S28	11	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and (Al with Ga with In with P) and (Al with Ga with As) and (MQW or (multi near2 quantum near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 13:00
S26	188	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 13:00
S30	6	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and (Al with Ga with In with P) and (Al with Ga with As) and (MQW or (multi near2 quantum near2 well)) and inject\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 13:06
S29	128	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 13:07
S31	56	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and "372"/\$.ccls. and (MQW or (multi near2 quantum near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:26
S35	1	laser and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB	AND	ON	2005/09/14 14:27
S34	1	laser and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:27
S33	8	laser and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:27
S32	8	(Semiconductor near3 laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and cap and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:27
S27	37	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and (Al with Ga with In with P) and (Al with Ga with As)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:46
S4	0	laser and (clad near3 (Al near3 Ga near3 In near3 P)) and (active near3 (Al near3 Ga near3 In near3 P)) and ((band near2 gap) or bandgap) near3 (Al near3 Ga near3 In near3 P)) and oxide and (cap near3 (Al near3 Ga near3 As)) and (contact near3 (Al near3 Ga near3 As))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 14:47

S38	0	laser and clad\$3 near4 ((Al with Ga with In with P) or (AlGaInP))) and (active near4 ((Al with Ga with In with P) or (AlGaInP))) and (((band near2 gap) or bandgap) near4 ((Al with Ga with In with P) or (AlGaInP))) and oxide and ((cap or (electron near2 block\$3)) near4 ((Al with Ga with As) or (AlGaAs))) and (contact near4 ((Al with Ga with As) or (AlGaAs)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:46
S39	7	laser and clad\$3 near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and (active near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and (((band near2 gap) or bandgap) near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and oxide and ((cap or (electron near2 block\$3)) near4 ((Al OR Ga OR As) or (AlGaAs))) and (contact near4 ((Al OR Ga OR As) or (AlGaAs)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:48
S41	3	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al with Ga with In with P) or (AlGaInP)) and ((Al with Ga with As) or (AlGaAs)) and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:49
S36	108	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al with Ga with In with P) or (AlGaInP)) and ((Al with Ga with As) or (AlGaAs))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:55
S42	476	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al OR Ga OR In OR P) or (Al with Ga with In with P) or (AlGaInP)) and ((Al OR Ga OR As) or (Al with Ga with As) or (AlGaAs))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:57
S40	0	laser and clad\$3 near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and (active near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and (((band near2 gap) or bandgap) near4 ((Al OR Ga OR In OR P) or (AlGaInP))) and oxide and ((cap or (electron near2 block\$3)) near4 ((Al OR Ga OR As) or (AlGaAs))) and (contact near4 ((Al OR Ga OR As) or (AlGaAs))) and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:58
S37	0	laser and clad\$3 near4 ((Al with Ga with In with P) or (AlGaInP))) and (activenear4 ((Al with Ga with In with P) or (AlGaInP))) and (((band near2 gap) or bandgap) near4 ((Al with Ga with In with P) or (AlGaInP))) and oxide and ((cap or (electron near2 block\$3)) near4 ((Al with Ga with As) or (AlGaAs))) and (contact near4 ((Al with Ga with As) or (AlGaAs)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 15:59
S45	0	S44 and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:05
S46	6	("20040066822" "5070510" "5573976" "5770471" "6356572" "6670202").PN. OR ("6882671").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/09/14 16:30
S44	7	laser and clad\$3 near4 ((Al with Ga with In with P) or (Al OR Ga OR In OR P) or (AlGaInP))) and (active near4 ((Al with Ga with In with P) or (Al OR Ga OR In OR P) or (AlGaInP))) and (((band near2 gap) or bandgap) near4 ((Al with Ga with In with P) or (Al OR Ga OR In OR P) or (AlGaInP))) and oxide and ((cap or (electron near2 block\$3)) near4 ((Al with Ga with As) or (Al OR Ga OR As) or (AlGaAs))) and (contact near4 ((Al with Ga with As) or (Al OR Ga OR As) or (AlGaAs)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:42
S43	8	(laser) and clad\$4 and active and ((band near2 gap) or bandgap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al OR Ga OR In OR P) or (Al with Ga with In with P) or (AlGaInP)) and ((Al OR Ga OR As) or (Al with Ga with As) or (AlGaAs)) and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:45

S47	8	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al OR Ga OR In OR P) or (Al with Ga with In with P) or (AlGaInP)) and ((Al OR Ga OR As) or (Al with Ga with As) or (AlGaAs)) and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:46
S49	3	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) and oxide and (cap or (electron near2 block\$3)) and contact and ((Al with Ga with In with P) or (AlGaInP)) and ((Al with Ga with As) or (AlGaAs)) and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:47
S50	2	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) with oxide) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:56
S48	8	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) and oxide and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:56
S52	3	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) same oxid\$4) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:57
S51	2	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) same oxide) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 16:57
S53	3	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) with oxid\$4) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 17:01
S54	3	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) with oxid\$5) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 17:20

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L1	1	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) with oxid\$5) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/14 17:21
L2	1	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) with oxid\$5) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB	AND	ON	2005/09/14 17:21
L3	1	(laser) and clad\$4 and active and (((band near2 gap) or bandgap or band-gap) same oxid\$5) and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB	AND	ON	2005/09/14 17:21
L4	2	(laser) and clad\$4 and active and ((band near2 gap) or bandgap or band-gap) and oxid\$5 and (cap or (electron near2 block\$3)) and contact and inject\$3 and (noninject\$4 or non-inject\$4).clm.	US-PGPUB	AND	ON	2005/09/14 17:21



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- Combine search queries using AND, OR, or NOT
- Delete a search
- Run a search

Recent Search Queries

	Results
<u>#1</u> ((laser and (clad or claddint) and active and non-inject\$ and inject\$ and oxide and (contact or electrode) and cap) <in>metadata)	0
<u>#2</u> ((laser and (clad or claddint) and active and inject\$ and oxide and (contact or electrode) and cap)<in>metadata)	0
<u>#3</u> (laser and (clad\$) and active and inject\$ and oxide and (contact or electrode) and cap)<in>metadata)	0
<u>#4</u> (laser and clad\$ and active and inject\$ and oxide and contact and cap)<in>metadata)	0
<u>#5</u> (laser and clad\$ and active and oxide and contact and cap) <in>metadata)	0
<u>#6</u> (laser and clad\$ and active and oxide and contact and cap) <in>metadata)	0
<u>#7</u> (laser and clad\$ and active and oxide and contact and cap) <in>metadata)	0
<u>#8</u> laser and clad\$ and active and cap and contact	119
<u>#9</u> (laser and clad\$ and active and cap and contact and oxide<IN>metadata)	5
(laser and clad\$ and active and cap and contact and	

#10	oxide<N>metadata)	5
#11	(laser and clad\$ and active and cap and contact and inject and oxide<in>metadata)	3
#12	(laser and clad\$ and active and cap and contact and inject and oxide<in>metadata)	3
#13	(laser and clad\$ and active and cap and contact and inject\$ and oxide<in>metadata)	3
#14	(laser and clad\$ and active and cap and contact and non-inject\$ and inject\$ and oxide<in>metadata)	0
#15	(laser and clad\$ and active and cap and contact and non-inject\$ and inject\$ and oxide<in>metadata)	0
#16	(laser and clad\$ and active and cap and contact and (bandgap or band gap) and inject\$ and oxide<in>metadata)	1
#17	(laser and clad\$ and active and cap and contact and (bandgap or band gap) and inject\$ and oxide<in>metadata)	1

